

ABSTRACT OF THE DISCLOSURE

5 A semiconductor device includes a semiconductor layer of a first conductive type formed in an active region, a first gate electrode formed on the semiconductor layer via a gate insulating film in a predetermined pattern, a first insulating mask formed on at least a part of the first gate electrode and a part of the semiconductor layer, and a pair of first diffusion regions of a second conductive type formed in 10 the active region not covered with the first insulating mask and first gate electrode. The pair of first diffusion regions is positioned adjacent to the first gate electrode and being used as a source and drain.

10025764.1.19904